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## NTE2592 Silicon NPN Transistor Horizontal Output for HDTV TO-220 Full Pack

**Features:**

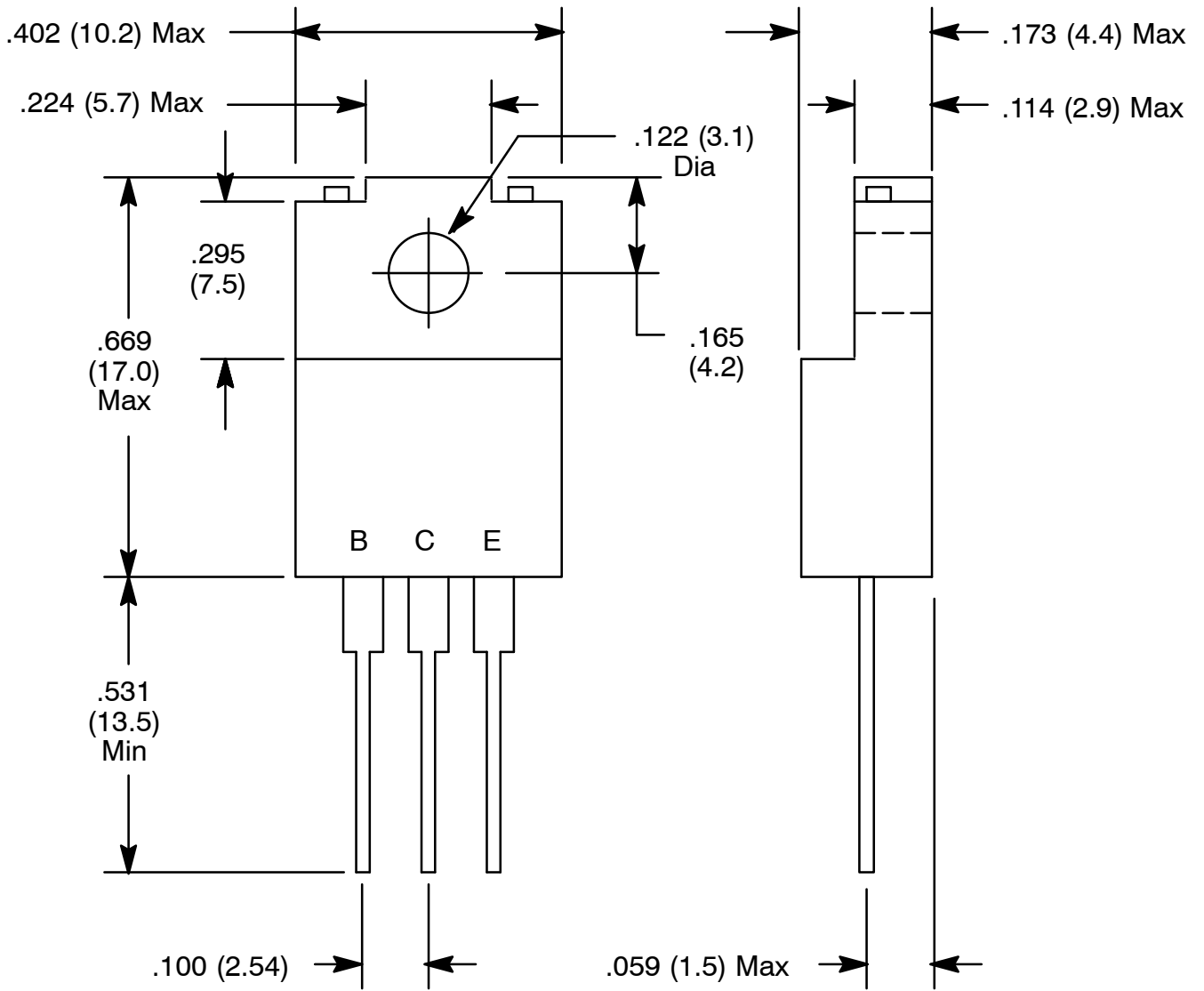
- High Breakdown Voltage:  $V_{(BR)CBO} = 2000V$  Min

**Absolute Maximum Ratings:** ( $T_C = +25^\circ C$  unless otherwise specified)

Collector-Base Voltage, $V_{CBO}$ .....	2000V
Collector-Emitter Voltage, $V_{CEO}$ .....	1800V
Emitter-Base Voltage, $V_{EBO}$ .....	5V
Collector Current, $I_C$	
Continuous .....	15mA
Peak .....	50mA
Collector Power Dissipation, $P_C$ .....	2W
Junction Temperature Range, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	-55° to +150°C
Maximum Thermal Resistance, Junction-to-Case, $R_{thJC}$ .....	8.3°C/W

**Electrical Characteristics:** ( $T_C = +25^\circ C$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 1800V, I_E = 0$	-	-	1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4V, I_C = 0$	-	-	1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = 5V, I_C = 300\mu A$	10	-	60	
Gain Bandwidth Product	$f_T$	$V_{CE} = 10V, I_C = 300\mu A$	-	6	-	MHz
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 600\mu A, I_B = 120\mu A$	-	-	5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 600\mu A, I_B = 120\mu A$	-	-	2	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	2000	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100\mu A, R_{BE} = \infty$	1800	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5	-	-	V
Output Capacitance	$C_{ob}$	$V_{CB} = 100V, f = 1MHz$	-	1.8	-	pF



**NOTE:** Tab is isolated